

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

#2 pre Amended
8-15-02
Rothko

In re Application of:

Docket No. 25740-02A

Feng-Tso Chien

Serial No.: To be assigned

Date Filed: Concurrently herewith

Title: Power Mosfet Device With Reduced Snap-Back and
Being Capable of Increasing Avalanche-Breakdown
Current Endurance, and Method of Manufacturing
Same

Box Patent Application
U.S. Patent and Trademark Office
P.O. Box 2327
Arlington, VA 22202

PRELIMINARY AMENDMENT

Prior to issuing a first office action, please amend the
application as follows:

IN THE CLAIMS

Please add new claims 3-8 as follows:

3. (New) A power MOSFET device comprising:
- an N⁺ silicon substrate;
 - a gate electrode;
 - an N⁻ epitaxial layer formed above said N⁺ silicon
substrate, at least a portion of which is intermediate the N⁺
silicon substrate and the gate electrode;
 - a P⁻ well implanted in the N⁻ epitaxial layer;